

#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
001	$32m\Omega$ @ $V_{GS} = -4.5V$	-13A
-20V	53mΩ @ V <sub>GS</sub> = -2.5V	-10A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

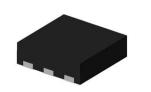
## **Features and Benefits**

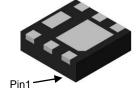
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

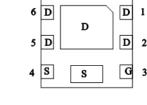
### **Mechanical Data**

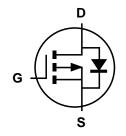
- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 €
- Weight: 0.0065 grams (Approximate)

### U-DFN2020-6 (Type F)









Top View

**Bottom View** 

Pin Out Bottom View

Equivalent Circuit

### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP2040UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP2040UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



4D = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		Е	F		G	Н			J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
WOILLI	Jan	i en	iviai	761	iviay	Juli	Jui	Aug	Sep	OCI	INOV	Dec



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	-20	V		
Gate-Source Voltage	$V_{GSS}$	±12	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-6.1 -4.9	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-13 -10	А		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-35	Α		
Continuous Source-Drain Diode Current (Note 6)	Is	-2.0	Α		
Avalanche Current (Note 8) L = 0.1mH	I <sub>AS</sub>	-17	Α		
Avalanche Energy (Note 8) L = 0.1mH			E <sub>AS</sub>	14	mJ

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	$P_{D}$	0.8	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	149	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	t<10s R <sub>θJA</sub>		C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	$P_{D}$	1.8	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	70	°C/W	
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	45	C/VV	
Thermal Resistance, Junction to Case (Note 7)	Steady State	R <sub>0JC</sub>	16	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# **Electrical Characteristics** (T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)			•	•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_		V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 9)			•	•			
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.6	_	-1.5	V	$V_{DS} = V_{GS}, I_{D} = -250\mu A$	
Static Drain-Source On-Resistance	D	_	22	32	mΩ	$V_{GS} = -4.5V$ , $I_D = -8.9A$	
Static Diani-Source On-Resistance	R <sub>DS(ON)</sub>	_	31	53	11122	$V_{GS} = -2.5V, I_D = -6.9A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -2.9A$	
DYNAMIC CHARACTERISTICS (Note 10)			•	•			
Input Capacitance	C <sub>iss</sub>	_	834	_		101/11/	
Output Capacitance	Coss	_	133	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	105	_		1 = 1.0W112	
Gate Resistance	R <sub>G</sub>	_	4.9		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	8.6				
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg	_	19		nC	N/ 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	
Gate-Source Charge	Q <sub>gs</sub>	_	1.5	_	IIC	$V_{DS} = -6V, I_{D} = -8.9A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	2.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.8	_			
Turn-On Rise Time	t <sub>R</sub>	_	7.7	_		$V_{DD} = -6V, R_L = 6\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	28.1	_	ns	$V_{GS} = -4.5V, R_G = 6\Omega, I_D = -1A$	
Turn-Off Fall Time	t <sub>F</sub>	_	14.6	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	9.8	_	ns	$I_F = -8.9A$ , $di/dt = -100A/\mu s$	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	2.7	_	nC	$I_F = -8.9A$ , $di/dt = -100A/\mu s$	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

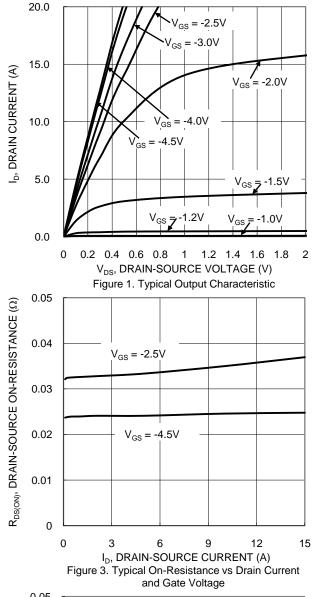
<sup>7.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).

<sup>8.</sup>  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25$ °C.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

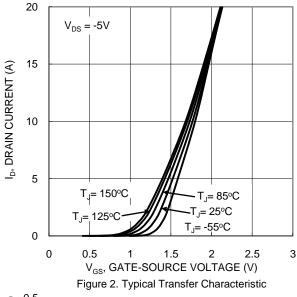


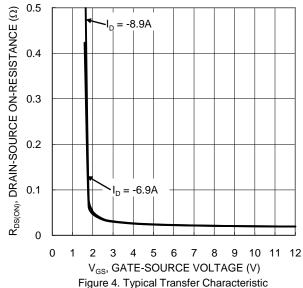




0.05 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE  $V_{GS} = -4.5V$ 0.04  $T_1 = 125^{\circ}C$ T<sub>.1</sub>= 85°C 0.03 T<sub>J</sub> = 25°C 0.02  $T_J = -55$ °C 0.01 0 0 10 20 15 I<sub>D</sub>, DRAIN CURRENT (A)

Figure 5. Typical On-Resistance vs Drain Current and Temperature





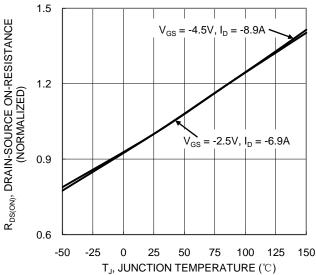
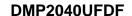
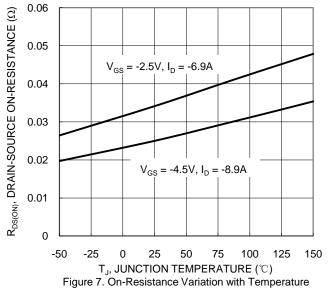
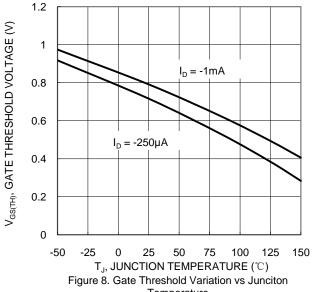


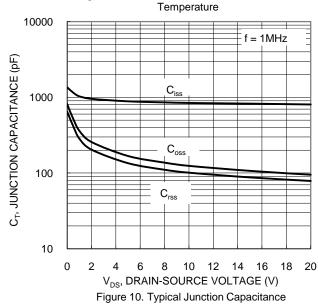
Figure 6. On-Resistance Variation with Temperature

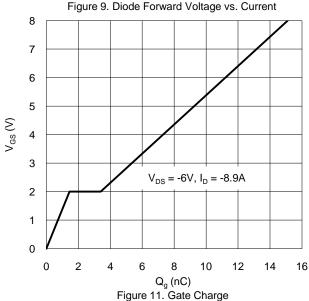


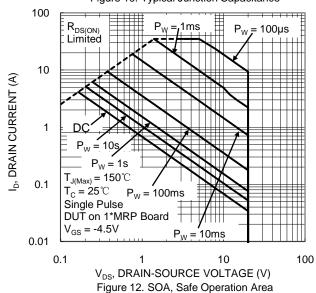














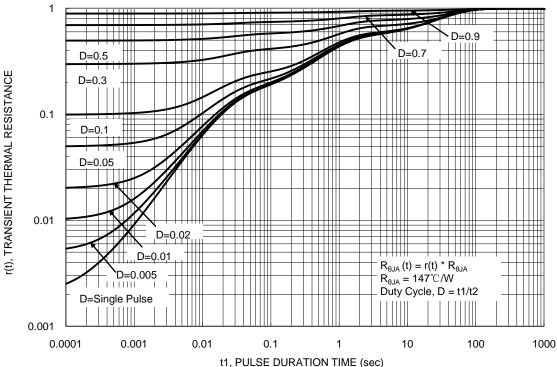


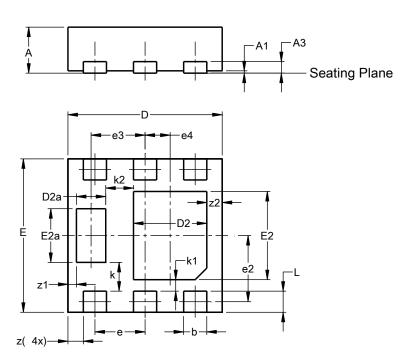
Figure 13. Transient Thermal Resistance



# **Package Outline Dimension**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

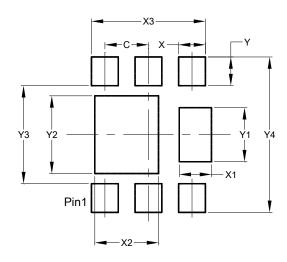


U-DFN2020-6							
(Type F)							
Dim	Min	Min Max Typ					
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	0.863 BSC						
е3	0.70 BSC						
e4	0.325 BSC						
k	0.37 BSC						
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
Z	0.20 BSC						
z1		).110 BS					
z2	0.20 BSC						
All C	imens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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